

**Amendment to Claims**

This listing of Claims will replace all prior versions and listings of claims in this Application.

**Listing of Claims**

Claim 1. (CURRENTLY AMENDED) A method of forming a MOS device on a silicon substrate, comprising:

preparing a substrate to contain a conductive region of a first conductivity type having a first device active area;

forming a gate electrode structure on the first device active area, said gate electrode structure including a gate electrode and insulating sidewalls;

implanting ions using a single mask and in a single implantation step of an opposite conductivity type from that of said first device active area into the exposed portions of said conductive region to form source and drain regions on opposite sides of said gate structure, wherein the source region includes a LDD source region underlying the insulating sidewall, and wherein the drain region includes a LDD drain region underlying the insulating sidewall; and

depositing by selective CVD a silicide layer over said source and drain regions and over said gate electrode.

Claim 2. (PREVIOUSLY AMENDED) The method of claim 1 in which said single implanting step includes implanting ions using plasma immersion ion implantation at an energy in a range of about 0.5 keV to 2 keV to form a shallow implant.

Claim 3. (PREVIOUSLY AMENDED) The method of claim 1 in which said

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implanting step includes implanting ions using plasma immersion ion implantation and includes implanting at a dose in a range of about  $1.0 \times 10^{14} \text{ cm}^{-2}$  to  $1.0 \times 10^{15} \text{ cm}^{-2}$  to form a MDD device.

Claim 4. (PREVIOUSLY AMENDED) The method of claim 1 in which said implanting step includes implanting ions using plasma immersion ion implantation and includes implanting to yield a surface ion concentration in said source and drain regions in a range of about  $1.0 \times 10^{19} \text{ cm}^{-3}$  to  $1.0 \times 10^{22} \text{ cm}^{-3}$  to form a shallow implant, MDD device.

Claim 5. (ORIGINAL) The method of claim 1 including, following said step of depositing a silicide layer by CVD, the steps of depositing an insulating layer over the structure and metallizing the structure.

Claims 6 - 10 CANCELLED

Claim 11. (CURRENTLY AMENDED) A method of forming a CMOS device on a silicon substrate, comprising:

preparing a substrate to contain a conductive region of a first type having a first device active area therein, and to contain a conductive region of a second type having a second device active area therein;

forming gate electrodes on the first and on the second active areas;

depositing and forming a gate electrode sidewall insulator layer on each gate electrode;

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masking the first device active area;

implanting ions using a single mask in a single implantation step of a first type into the exposed portions of the second device active area to form a source region and a drain region in the second device active area, wherein the second device source region includes a LDD source region underlying the insulating sidewall, and wherein the second device drain region includes a LDD drain region underlying the insulating sidewall;

stripping the mask;

masking the second device active area;

implanting ions of a second type into the exposed portions of the first device active area to form a source region and a drain region in the first device active area, wherein the first device source region includes a LDD source region underlying the insulating sidewall, and wherein the first device drain region includes a LDD drain region underlying the insulating sidewall;

stripping the mask; and

depositing a silicide layer over the gate electrodes and the source and drain regions in the first and second device active areas.

Claim 12. (ORIGINAL) The method of claim 11 wherein said implanting steps includes implanting ions using plasma immersion ion implantation.

Claim 13. (PREVIOUSLY AMENDED) The method of claim 12 wherein said implanting step includes implanting at an energy level in a range of between about 0.5 keV and 2 keV and a dose in a range of between about  $1.0 \times 10^{14} \text{ cm}^{-2}$  to  $1.0 \times 10^{15} \text{ cm}^{-2}$  to form a shallow

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implant, MDD device.

Claim 14. (PREVIOUSLY AMENDED) The method of claim 12 wherein said implanting step includes implanting to yield a surface ion concentration in said source and drain regions in a range of about  $1.0 \times 10^{19} \text{ cm}^{-3}$  to  $1.0 \times 10^{22} \text{ cm}^{-3}$  to form a shallow implant, MDD device.

Claim 15. (PREVIOUSLY AMENDED) The method of claim 11 wherein said step of depositing a silicide layer includes depositing a silicide layer by selective CVD of silicide only over the source region, drain region and gate electrode.

Claim 16. (ORIGINAL) The method of claim 11 including, following said step of depositing a silicide layer, the steps of depositing an insulating layer over the structure and metallizing the structure.

Claims 17 - 22 CANCELLED